## **ABSTRACT**

A method for making a semiconductor device is described. That method comprises forming a hard mask and an etch stop layer on a patterned sacrificial gate electrode layer.

After first and second spacers are formed on opposite sides of that patterned sacrificial layer, the patterned sacrificial layer is removed to generate a trench that is positioned between the first and second spacers. At least part of the trench is filled with a metal layer.